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02/11/02

U.S. UTILITY Patent Application

PATENT NUMBER and
ISSUE DATE

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10073506	02/11/2002	429	446	1775	Smith

**APPLICANT'S: Falster Robert; Binns Martin; Wang Alan;

**CONTINUING DATA VERIFIED:

THIS APPLICATION IS A DIV OF 09/416,998 10/13/1999
WHICH CLAIMS BENEFIT OF 60/104,304 10/14/1993

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** FOREIGN APPLICATIONS VERIFIED:

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		MEMO 98-1451/2554.1
Verified and Acknowledged Examiners's initials		
TITLE : Thermal annealing process for producing low defect density single crystal silicon		

U.S. DEPT. OF COMM./PAT. & TM. PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
ISSUE FEE		Sheets Drwg.	Figs. Drwg.
Amount Due	Date Paid	Print Fig.	
Primary Examiner		Application Examiner	
PREPARED FOR ISSUE			
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